

**AMENDMENTS TO THE SPECIFICATION**

Please amend the specification as follows on the identified pages:

**Page 41, third full paragraph:**

Figure 1A shows one embodiment of apparatus according to the sixth aspect of the present invention and Figure 1B shows the gate dielectric device that results from the method using the apparatus of Fig. 1A;

**Paragraph bridging pages 41 and 42:**

**Example 1 : Polymer - Monomer System**

As illustrated in Fig. 1B, a glass substrate 1 is prepatterned with 15-20-nm thick gold (with 3-nm-thick chromium adhesion layer) source-drain interdigitated array 2, 3. Channel length is 3 micron, channel width 10nm. The substrate is then cleaned by oxygen plasma (pressure of oxygen, 450 mbar; power 200 W; time, 10 min) in a barrier-type Plasmaline etcher, followed by Millipore water, then isopropanol rinse, and nitrogen blow-off. Hexamethyldisilazane is spun onto the substrate at 900 rpm, 30s, and then the substrate is baked in air on a hotplate for 2 min at 120°C.

**Page 42, second full paragraph:**

A solution of TFB-DVS-BCB-mesitylene (3:2:100 by weight) is then spin-cast onto the substrate at 1600 rpm in a controlled airflow environment (see Note 1 and Figure 1) to give a drying time of 30 s. The resultant film 4 comprises 60-nm-thick DVS-BCB 4b overlying 80-nm-thick TFB 4a.

**Page 43, first full paragraph:**

A PEDT:PSS top-gate electrode 5 is then printed onto the top dielectric surface in air, dried at 80°C, and then transferred to a nitrogen box to bake for 2 min on a hotplate at 160°C.